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INFORMATION DISCLOSURE CITATION	ATTY. DOCKET NO. <u>124-1158</u>	SERIAL NO. <u>301677933</u> <small>SEARCHED</small>
APPLICANT <u>PHILLIPS et al.</u>		
(Use several sheets if necessary)	FILING DATE <u>May 3, 2006</u>	TC/A.U. <u>unknown</u>

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS		SUBCLASS	FILING DATE IF APPROPRIATE
				CLASS	SUBCLASS		
MG	2003/080332 A1	05/2003	PHILLIPS				
MG	5,298,441 A	03/1994	GORONKIN et al.				
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MG		01/93337 A1	12/2001	WO				
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MG	International Search Report of PCT/GB2004/004722, mailed 31 January 2005
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MG	LOTT et al, "STRAINED <i>p</i> -CHANNEL InGaSb/AIGaSb MODULATION-DOPED FIELD-EFFECT TRANSISTORS", Electronics Letters, Vol. 28, No. 15, 16 July 1992, Pgs. 1459-1460, XP000307703
MG	Patent Abstracts of Japan, JP 01 009656 A, Vol. 13, No. 184, 12 January 1989
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MG	Patent Abstracts of Japan, JP 63 051678 A, Vol. 012, No. 268, 4 March 1988

*Examiner

/Mohammad Ghazzawi/

Date Considered

03/05/2007

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.